

#### **Features**

- Split Gate Trench MOSFET Technology
- Low R<sub>DS(on)</sub> & FOM
- Low Crss
- · Extremely Low Switching Loss
- · Excellent Stability and Uniformity
- · Moisture Sensitivity Level 1
- Halogen Free. "Green" Device (Note 1)
- Epoxy Meets UL 94 V-0 Flammability Rating
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)

# **Maximum Ratings**

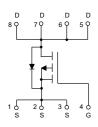
- Operating Junction Temperature Range : -55°C to +150°C
- Storage Temperature Range: -55°C to +150°C
- Thermal Resistance: 40°C/W Junction to Ambient(t≤10s)
- Thermal Resistance: 75°C/W Junction to Ambient(Steady-State)
- Thermal Resistance: 24°C/W Junction to Lead(Steady-State)

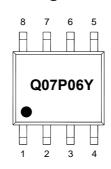
Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V <sub>DS</sub>	-60	V
Gate-Source Volltage	V <sub>GS</sub>	±20	V
Continuous Drain Current	I <sub>D</sub>	-7	Α
Pulsed Drain Current <sup>(2)</sup>	I <sub>DM</sub>	-30	Α
Total Power Dissipation <sup>(3)</sup>	P <sub>D</sub>	3.1	W
Single Pulsed Avalanche Energy <sup>(4)</sup>	E <sub>AS</sub>	81	mJ

#### Note:

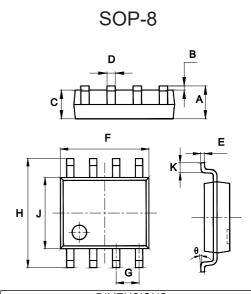
- 1. Halogen free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 2. Repetitive rating; pulse width limited by max. junction temperature.
- 3. P<sub>D</sub> is based on max. junction temperature, using junction-case thermal resistance.
- 4.  $V_{DD}$ =50V,  $R_{G}$ =25 $\Omega$ , L=0.5mH,  $I_{AS}$ =18A.

# **Internal Structure and Marking Code**



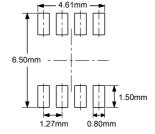


# P-CHANNEL MOSFET



DIMENSIONS					
DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	NOTE
Α	0.053	0.069	1.35	1.75	
В	0.004	0.010	0.10	0.25	
С	0.053	0.061	1.35	1.55	
D	0.013	0.020	0.33	0.51	
E	0.007	0.010	0.17	0.25	
F	0.185	0.200	4.70	5.10	
G	0.050		1.270		TYP.
Н	0.228	0.244	5.80	6.20	
J	0.150	0.157	3.80	4.00	
K	0.016	0.050	0.40	1.27	
θ	0°	8°	0°	8°	

# Suggested Solder Pad Layout 4.61mm →



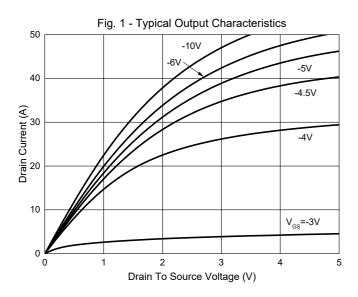


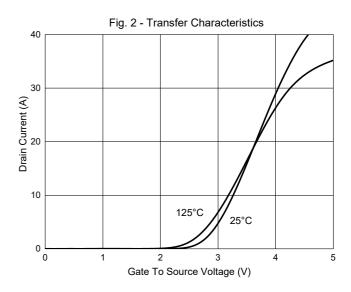
# Electrical Characteristics @ 25°C (Unless Otherwise Specified)

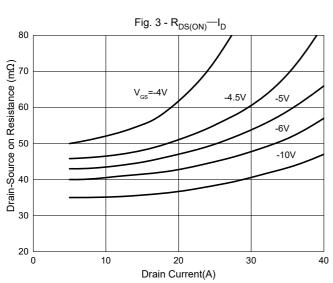
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static Characteristics			1	1	1		
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =-250μA	-60			V	
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>DS</sub> =0V, V <sub>GS</sub> =±20V			±100	nA	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-60V, V <sub>GS</sub> =0V			-1	μA	
Gate-Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250μA	-1.3	-1.8	-2.5	V	
Drain-Source On-Resistance	Ь	V <sub>GS</sub> =-10V, I <sub>D</sub> =-6A		35	47	mΩ	
Drain-Source On-Resistance	$R_{DS(on)}$	V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-3A		45	60	mΩ	
Diode Characteristics							
Continuous Body Diode Current	Is				-6	Α	
Diode Forward Voltage	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =-6A		-0.85	-1.3	V	
Reverse Recovery Time	t <sub>rr</sub>	1 04 11/11 4004/		20.2		ns	
Reverse Recovery Charge	Q <sub>rr</sub>	I <sub>S</sub> =-3A,di/dt=100A/μs		8.2		nC	
Dynamic Characteristics	•		·				
Input Capacitance	C <sub>iss</sub>			1100			
Output Capacitance	C <sub>oss</sub>	V <sub>DS</sub> =-30V,V <sub>GS</sub> =0V,f=1MHz		350		pF	
Reverse Transfer Capacitance	C <sub>rss</sub>			28			
Total Gate Charge	$Q_g$			18.7			
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS}$ =-30V, $V_{GS}$ =-10V, $I_{D}$ =-3A		4.7		nC	
Gate-Drain Charge	$Q_{gd}$			3.0			
Turn-On Delay Time	t <sub>d(on)</sub>			7.5			
Turn-On Rise Time	t <sub>r</sub>	V <sub>DS</sub> =-30V, V <sub>GS</sub> =-10V,		39.5		no	
Turn-Off Delay Time	t <sub>d(off)</sub>	$R_G=6\Omega$		43.6		ns	
Turn-Off Fall Time	t <sub>f</sub>			55.1			

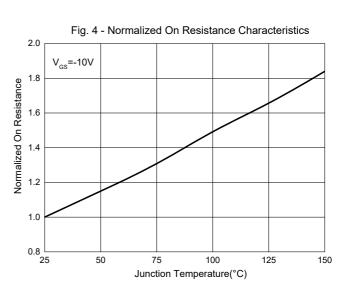


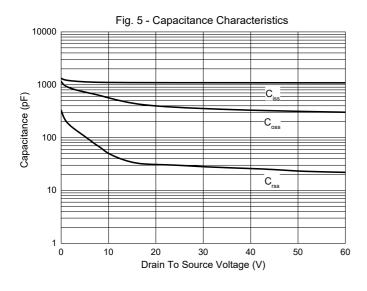
### **Curve Characteristics**

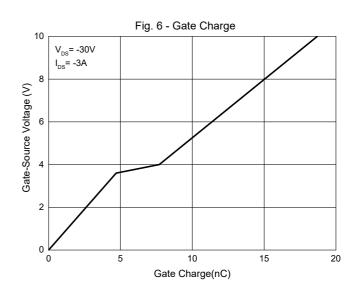






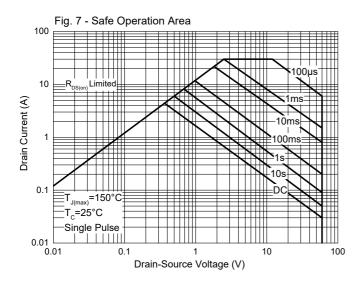


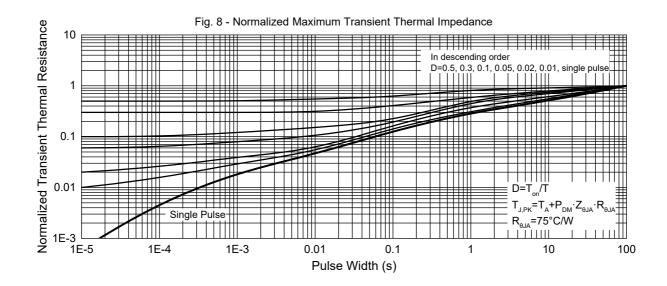






### **Curve Characteristics**







## **Ordering Information**

Device	Packing
Part Number-TP	Tape&Reel: 4Kpcs/Reel

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